## 1. General description

NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS301PX.

## 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

## 3. Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- · Power switches (e.g. motors, fans)

## 4. Quick reference data

#### Table 1. Quick reference data

| Symbol             | Parameter                               | Conditions   |  | Min | Тур | Max  | Unit |
|--------------------|---|--|--|-----|-----|------|------|
| V <sub>CEO</sub>   | collector-emitter voltage               | open base  |  | -   | -   | 12   | V    |
| I <sub>C</sub>     | collector current                       |  |  | -   | -   | 5.3  | A    |
| I <sub>CM</sub>    | peak collector current                  | single pulse; t <sub>p</sub> ≤ 1 ms  |  | -   | -   | 10.6 | A    |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C |  | -   | 28  | 40   | mΩ   |



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## 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | E      | emitter     |                    | С              |
| 2   | С      | collector   |                    |                |
| 3   | В      | base        |                    | B — [          |
|     |        |             | 3 2 1              | E              |
|     |        |             | SOT89              | sym123         |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number | Package |  |         |  |  |
|-------------|---------|--|---------|--|--|
|             | Name    | Description  | Version |  |  |
| PBSS301NX   | SOT89   | plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body | SOT89   |  |  |

## 7. Marking

#### Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PBSS301NX   | %5B             |

[1] % = placeholder for manufacturing site code

## 8. Limiting values

#### Table 5. Limiting values

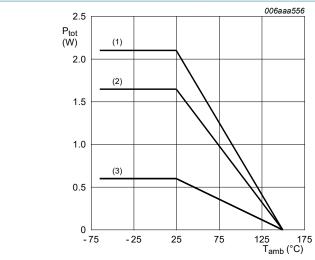
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Max  | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| $V_{CBO}$        | collector-base voltage    | open emitter                        |     | -   | 12   | V    |
| $V_{CEO}$        | collector-emitter voltage | open base                           |     | -   | 12   | V    |
| $V_{EBO}$        | emitter-base voltage      | open collector                      |     | -   | 5    | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | 5.3  | А    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 10.6 | А    |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 0.6  | W    |
|                  |                           |                                     | [2] | -   | 1.65 | W    |
|                  |                           |                                     | [3] | -   | 2.1  | W    |
| T <sub>j</sub>   | junction temperature      |                                     |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -65 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150  | °C   |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol   | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|--|--|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> thermal resistance from junction to ambient | thermal resistance from                          | in free air | [1] | -   | -   | 208 | K/W  |
|  |  | [2]         | -   | -   | 76  | K/W |      |
|  |  |             | [3] | -   | -   | 60  | K/W  |
| R <sub>th(j-sp)</sub>  | thermal resistance from junction to solder point |             |     | -   | -   | 20  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

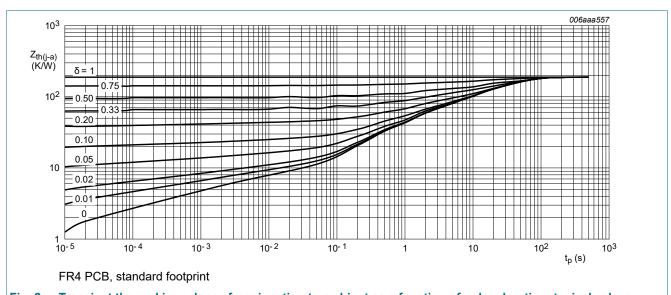


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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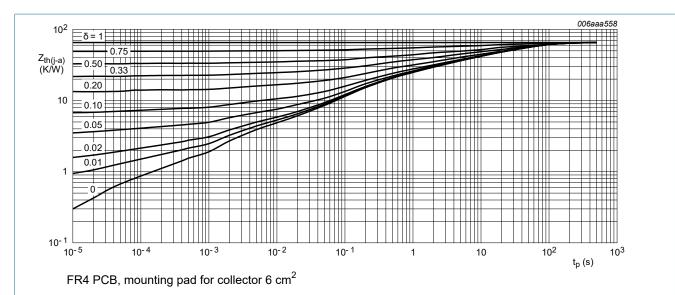


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

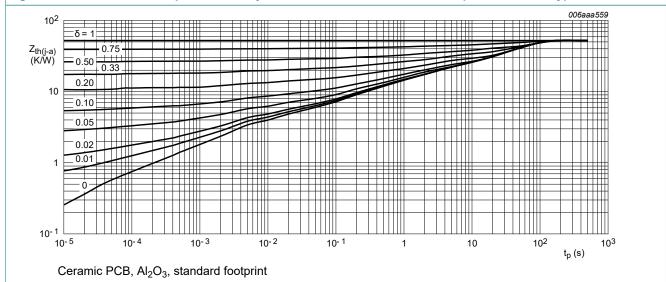


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 12 V, 5.3 A NPN low VCEsat (BISS) transistor

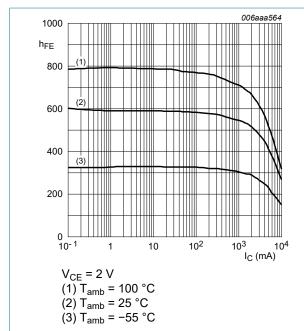
# 10. Characteristics

**Table 7. Characteristics** 

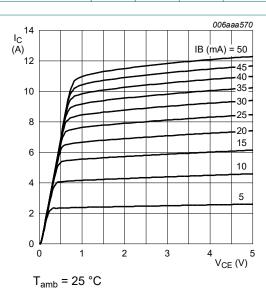
| Symbol             | Parameter                               | Conditions   | Min | Тур  | Max  | Unit |
|--------------------|---|--|-----|------|------|------|
| I <sub>CBO</sub>   | collector-base cut-off                  | V <sub>CB</sub> = 12 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C                                 | -   | -    | 100  | nA   |
|                    | current                                 | V <sub>CB</sub> = 12 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C                                  | -   | -    | 50   | μΑ   |
| I <sub>EBO</sub>   | emitter-base cut-off current            | V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C                                  | -   | -    | 100  | nA   |
| h <sub>FE</sub>    | DC current gain                         | $V_{CE}$ = 2 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                 | 300 | 530  | -    |      |
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C            | 300 | 520  | -    |      |
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ;<br>δ ≤ 0.02; $T_{amb}$ = 25 °C        | 250 | 480  | -    |      |
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 4 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C            | 200 | 420  | -    |      |
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 6 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C            | 200 | 340  | -    |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage    | $I_C$ = 0.5 A; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                    | -   | 18   | 25   | mV   |
|                    |   | $I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                      | -   | 35   | 50   | mV   |
|                    |   | $I_C$ = 1 A; $I_B$ = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                      | -   | 50   | 70   | mV   |
|                    |   | $I_C$ = 2 A; $I_B$ = 40 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                        | -   | 70   | 100  | mV   |
|                    |   | $I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                     | -   | 110  | 160  | mV   |
|                    |   | $I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                     | -   | 100  | 140  | mV   |
|                    |   | $I_C$ = 4 A; $I_B$ = 40 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                        | -   | 125  | 190  | mV   |
|                    |   | $I_C$ = 5.3 A; $I_B$ = 265 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                   | -   | 140  | 200  | mV   |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                     | -   | 28   | 40   | mΩ   |
|                    |   | $I_C$ = 4 A; $I_B$ = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                      | -   | 32   | 48   | mΩ   |
| V <sub>BEsat</sub> | base-emitter saturation voltage         | $I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                     | -   | 0.81 | 0.9  | V    |
|                    |   | $I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C            | -   | 0.92 | 1.05 | V    |
| $V_{BEon}$         | base-emitter turn-on voltage            | $V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C | -   | 0.75 | 0.85 | V    |
| t <sub>d</sub>     | delay time                              | V <sub>CC</sub> = 12.5 V; I <sub>C</sub> = 3 A; I <sub>Bon</sub> = 0.15 A;                             | -   | 15   | -    | ns   |
| t <sub>r</sub>     | rise time                               | I <sub>Boff</sub> = -0.15 A; T <sub>amb</sub> = 25 °C  | -   | 40   | -    | ns   |
| t <sub>on</sub>    | turn-on time                            | 1  | -   | 55   | -    | ns   |
| -s                 | storage time                            | 1  | -   | 195  | -    | ns   |
| t <sub>f</sub>     | fall time                               |  | -   | 75   | -    | ns   |
| t <sub>off</sub>   | turn-off time                           | 1  | -   | 270  | -    | ns   |

#### 12 V, 5.3 A NPN low VCEsat (BISS) transistor

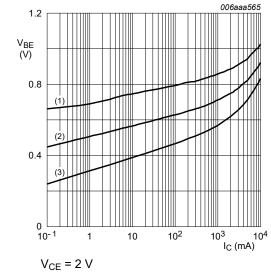
| Symbol         | Parameter             | Conditions  | Min | Тур | Max | Unit |
|----------------|-----------------------|---|-----|-----|-----|------|
| f <sub>T</sub> | transition frequency  | V <sub>CE</sub> = 10 V; I <sub>C</sub> = 3 A; f = 100 MHz;<br>T <sub>amb</sub> = 25 °C                          | -   | 140 | -   | MHz  |
| C <sub>c</sub> | collector capacitance | $V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $<br>$T_{amb} = 25 \text{ °C}$ | -   | 125 | 160 | pF   |



DC current gain as a function of collector Fig. 5. current; typical values



Collector current as a function of collector-Fig. 6. emitter voltage; typical values

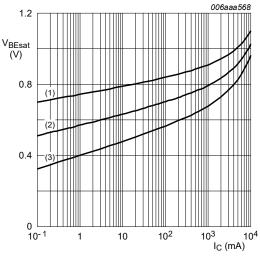


(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb}$  = 100 °C

Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb}$  = 100 °C

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

#### 12 V, 5.3 A NPN low VCEsat (BISS) transistor

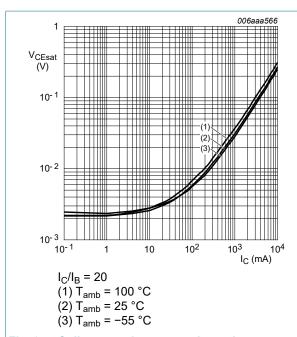


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

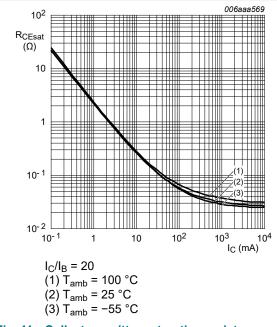


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

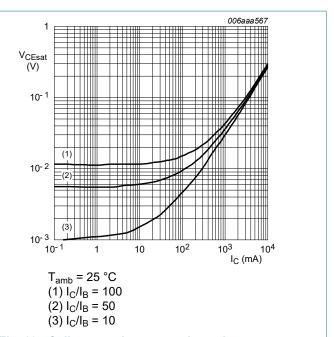


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

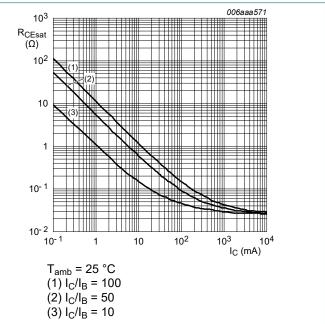


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

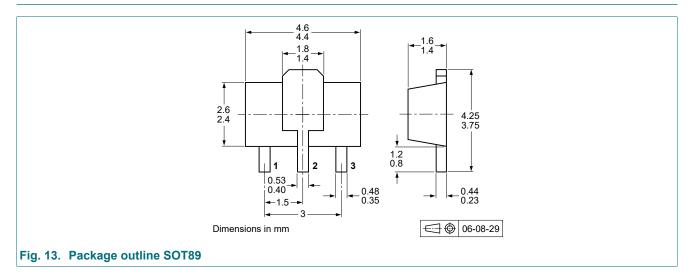
### 11. Test information

### **Quality information**

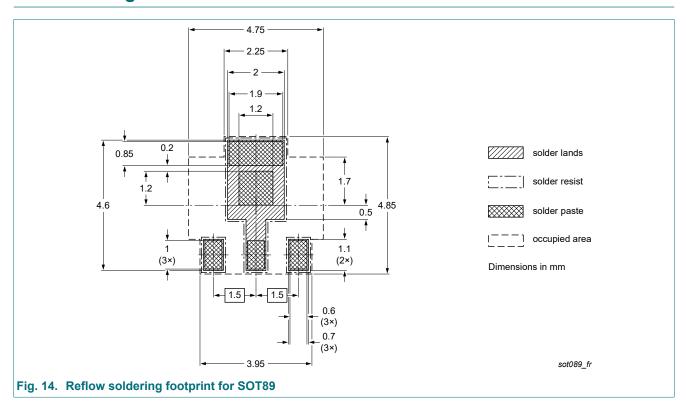
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12 V, 5.3 A NPN low VCEsat (BISS) transistor

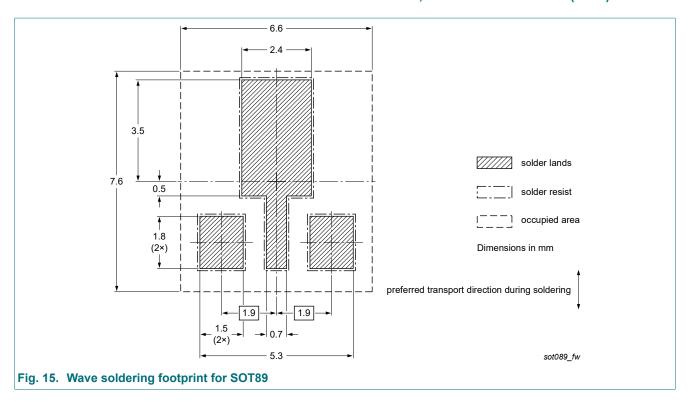
# 12. Package outline



## 13. Soldering



### 12 V, 5.3 A NPN low VCEsat (BISS) transistor



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# 14. Revision history

#### **Table 8. Revision history**

| Data sheet ID  | Release date  | Data sheet status  | Change notice | Supersedes    |  |
|----------------|---|--------------------|---------------|---------------|--|
| PBSS301NX v.3  | 20240206  | Product data sheet | -             | PBSS301NX v.2 |  |
| Modifications: | <ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Section "Packing information" removed.</li> </ul> |                    |               |               |  |
| PBSS301NX v.2  | 20091117  | Product data sheet | -             | PBSS301NX v.1 |  |
| PBSS301NX v.1  | 20060822  | Product data sheet | -             | -             |  |

## 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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PBSS301NX

### 12 V, 5.3 A NPN low VCEsat (BISS) transistor

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 6 February 2024

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